

Title (en)

METHOD FOR PRODUCING AN ELECTROMAGNETIC RADIATION-EMITTING SEMICONDUCTOR CHIP AND A CORRESPONDING ELECTROMAGNETIC RADIATION-EMITTING SEMICONDUCTOR CHIP

Title (de)

VERFAHREN ZUM HERSTELLEN EINES ELEKTROMAGNETISCHE STRAHLUNG EMITTIERENDEN HALBLEITERCHIPS UND ELEKTROMAGNETISCHE STRAHLUNG EMITTIERENDER HALBLEITERCHIP

Title (fr)

PROCEDE DE FABRICATION D'UNE PUCE A SEMICONDUCTEURS EMETTANT UN RAYONNEMENT ELECTROMAGNETIQUE ET PUCE A SEMICONDUCTEURS EMETTANT UN RAYONNEMENT ELECTROMAGNETIQUE

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Application

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Abstract (en)

[origin: WO2004021457A2] The invention relates to a method for producing a radiation-emitting semiconductor chip based on AlGaInP, comprising the following steps: preparing a substrate; applying a series of semiconductor layers to the substrate, said series of layers containing a photon-emitting active layer, and; applying a transparent decoupling layer comprising $Gax(InyAl1-y)1-xP$, whereby $0.8 \leq x$ and $0 \leq y \leq 1$. The invention provides that the substrate is made from germanium and that the transparent decoupling layer is applied at a low temperature.

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